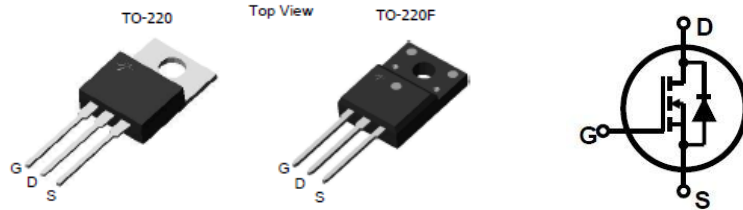


N-channel MOSFET

## Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- Halogen free package
- JEDEC Qualification

$BV_{DSS}$	$I_D$	$R_{DS(on)}$
500V	18A	< 0.3 $\Omega$



Device	Package	Marking	Remark
TMP20N50A / TMPF20N50A	TO-220 / TO-220F	TMP20N50A / TMPF20N50A	RoHS
TMP20N50AG / TMPF20N50AG	TO-220 / TO-220F	TMP20N50AG / TMPF20N50AG	Halogen Free

## Absolute Maximum Ratings

Parameter	Symbol	TMP20N50A(G)	TMPF20N50A(G)	Unit	
Drain-Source Voltage	$V_{DSS}$	500		V	
Gate-Source Voltage	$V_{GS}$	$\pm 30$		V	
Continuous Drain Current	$I_D$	$T_C = 25\text{ }^\circ\text{C}$	18	18 *	A
		$T_C = 100\text{ }^\circ\text{C}$	12.4	12.4 *	A
Pulsed Drain Current (Note 1)	$I_{DM}$	72	72 *	A	
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	705		mJ	
Repetitive Avalanche Current (Note 1)	$I_{AR}$	18		A	
Repetitive Avalanche Energy (Note 1)	$E_{AR}$	29		mJ	
Power Dissipation	$P_D$	$T_C = 25\text{ }^\circ\text{C}$	290	48	W
		Derate above 25 $^\circ\text{C}$	2.32	0.38	W/ $^\circ\text{C}$
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V/ns	
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150		$^\circ\text{C}$	
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	$T_L$	300		$^\circ\text{C}$	

\* Limited only by maximum junction temperature

## Thermal Characteristics

Parameter	Symbol	TMP20N50A(G)	TMPF20N50A(G)	Unit
Maximum Thermal resistance, Junction-to-Case	$R_{\theta JC}$	0.43	2.6	$^\circ\text{C}/\text{W}$
Maximum Thermal resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	62.5	$^\circ\text{C}/\text{W}$

**Electrical Characteristics :  $T_C=25^\circ\text{C}$ , unless otherwise noted**

Parameter	Symbol	Test condition	Min	Typ	Max	Units
<b>OFF</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
Forward Gate-Source Leakage Current	$I_{GSSF}$	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
Reverse Gate-Source Leakage Current	$I_{GSSR}$	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**ON**

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3	--	5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 9\text{ A}$	--	0.25	0.30	$\Omega$
Forward Transconductance <sup>(Note 4)</sup>	$g_{FS}$	$V_{DS} = 30\text{ V}, I_D = 9\text{ A}$	--	14	--	S

**DYNAMIC**

Input Capacitance	$C_{iss}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2880	--	pF
Output Capacitance	$C_{oss}$		--	283	--	pF
Reverse Transfer Capacitance	$C_{rss}$		--	10	--	pF

**SWITCHING**

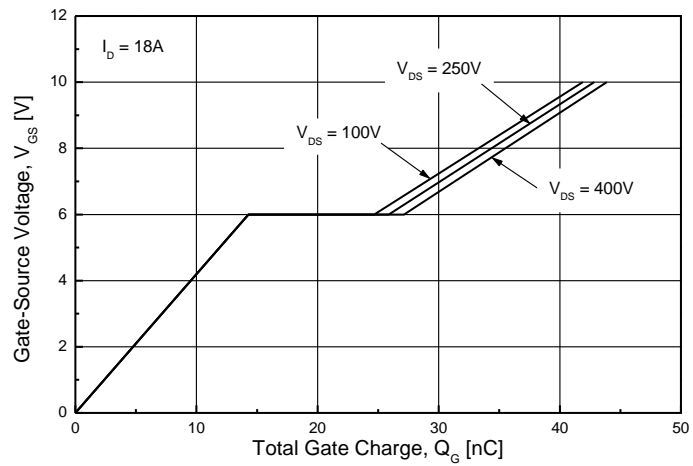
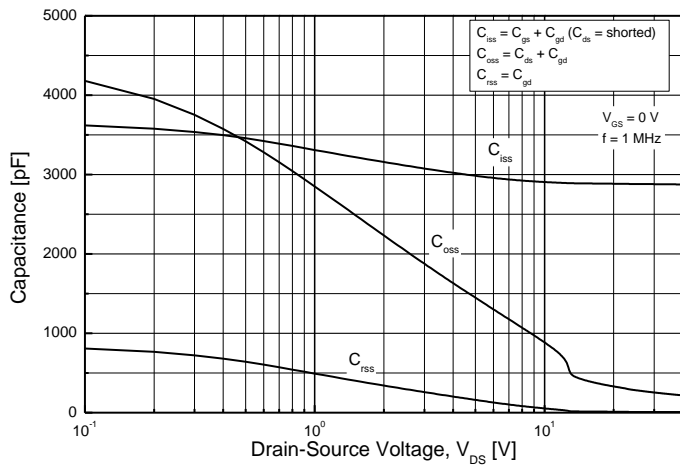
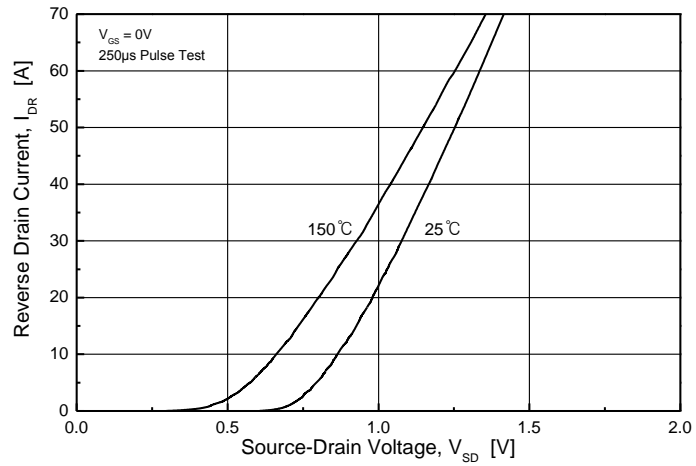
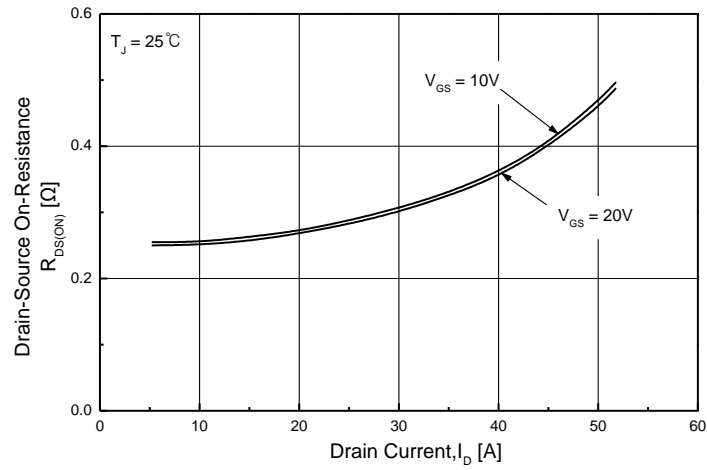
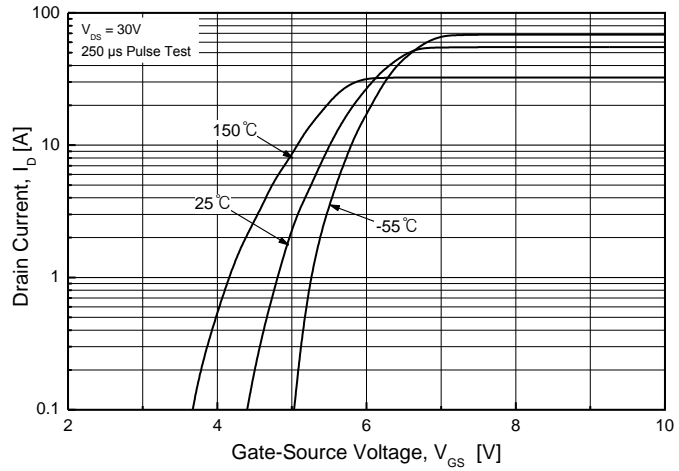
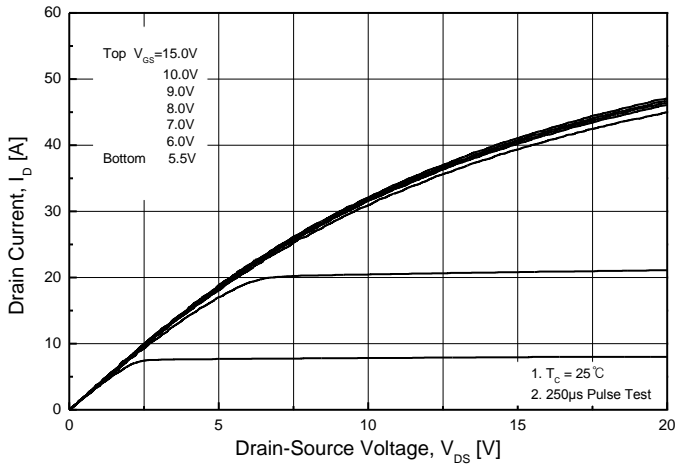
Turn-On Delay Time <sup>(Note 4,5)</sup>	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 18\text{ A},$ $R_G = 25\ \Omega$	--	64	--	ns
Turn-On Rise Time <sup>(Note 4,5)</sup>	$t_r$		--	61	--	ns
Turn-Off Delay Time <sup>(Note 4,5)</sup>	$t_{d(off)}$		--	123	--	ns
Turn-Off Fall Time <sup>(Note 4,5)</sup>	$t_f$		--	38	--	ns
Total Gate Charge <sup>(Note 4,5)</sup>	$Q_g$	$V_{DS} = 400\text{ V}, I_D = 18\text{ A},$ $V_{GS} = 10\text{ V}$	--	44	--	nC
Gate-Source Charge <sup>(Note 4,5)</sup>	$Q_{gs}$		--	14	--	nC
Gate-Drain Charge <sup>(Note 4,5)</sup>	$Q_{gd}$		--	13	--	nC

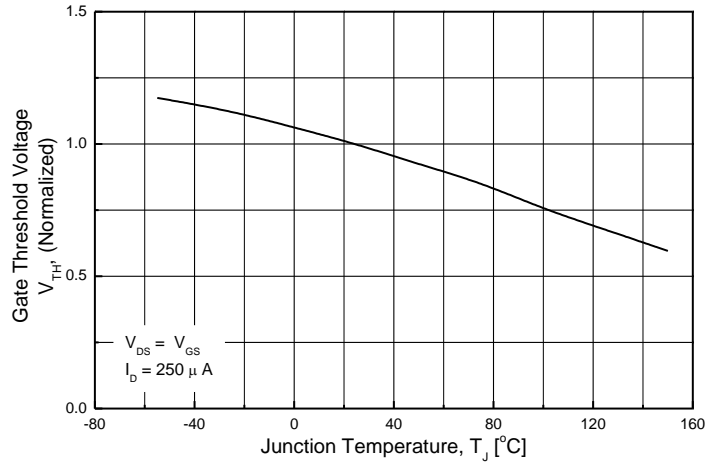
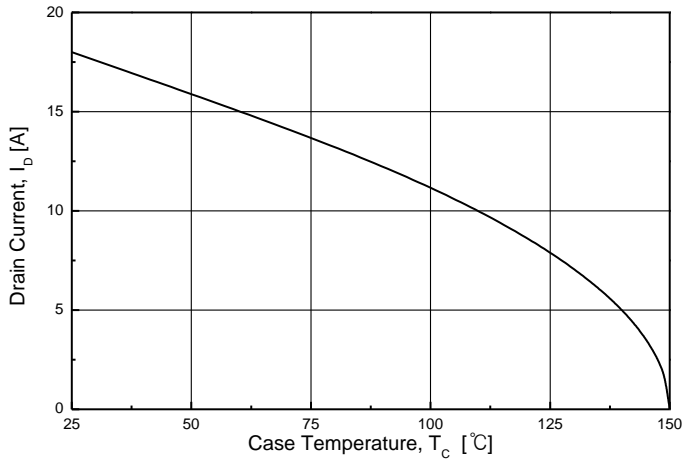
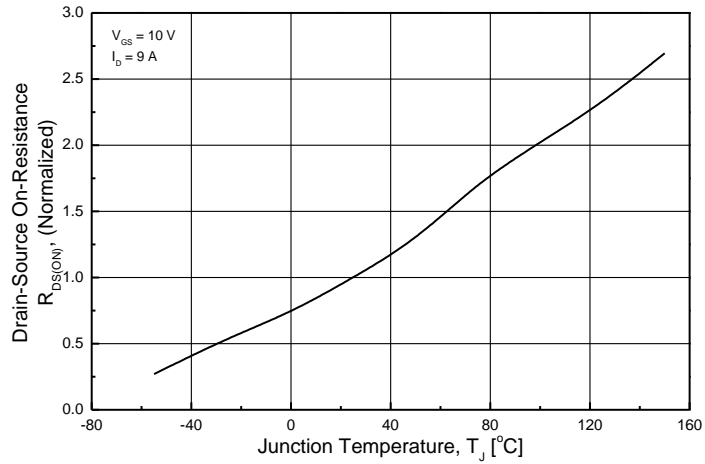
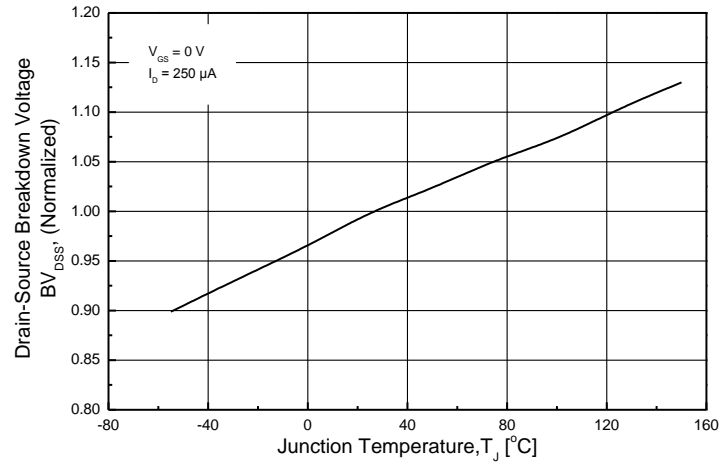
**SOURCE DRAIN DIODE**

Maximum Continuous Drain-Source Diode Forward Current	$I_S$	---	--	--	18	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$	---	--	--	72	A
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 18\text{ A}$	--	--	1.5	V
Reverse Recovery Time <sup>(Note 4)</sup>	$t_{rr}$	$V_{GS} = 0\text{ V}, I_S = 18\text{ A}$ $di_F / dt = 100\text{ A}/\mu\text{s}$	--	421	--	ns
Reverse Recovery Charge <sup>(Note 4)</sup>	$Q_{rr}$		--	5.9	--	$\mu\text{C}$

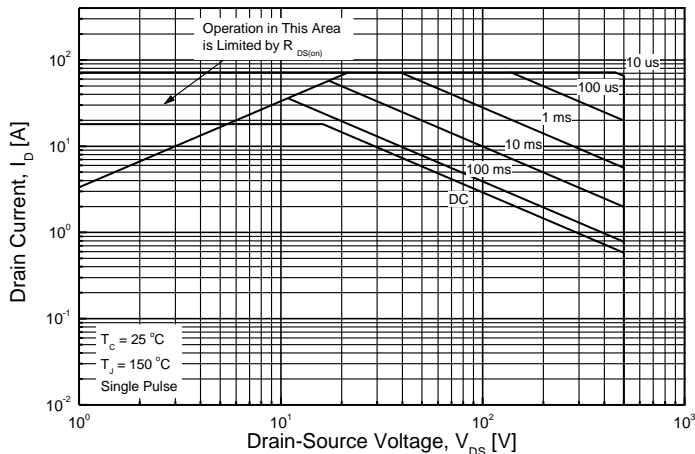
Note :

1. Repeated rating : Pulse width limited by safe operating area
2.  $L=4.6\text{mH}, I_{AS} = 18\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 18\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

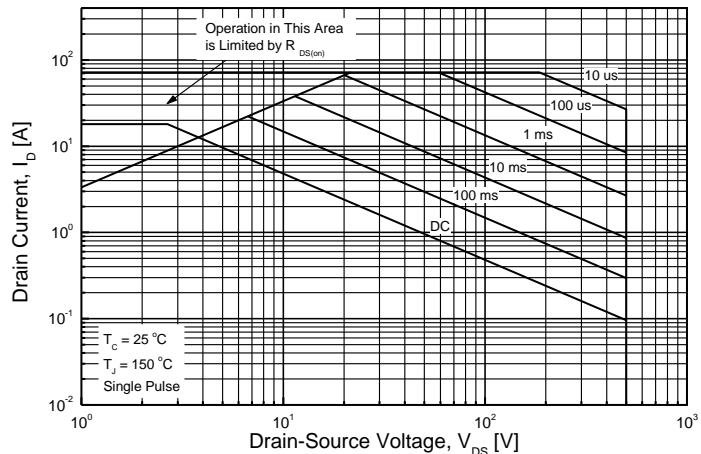


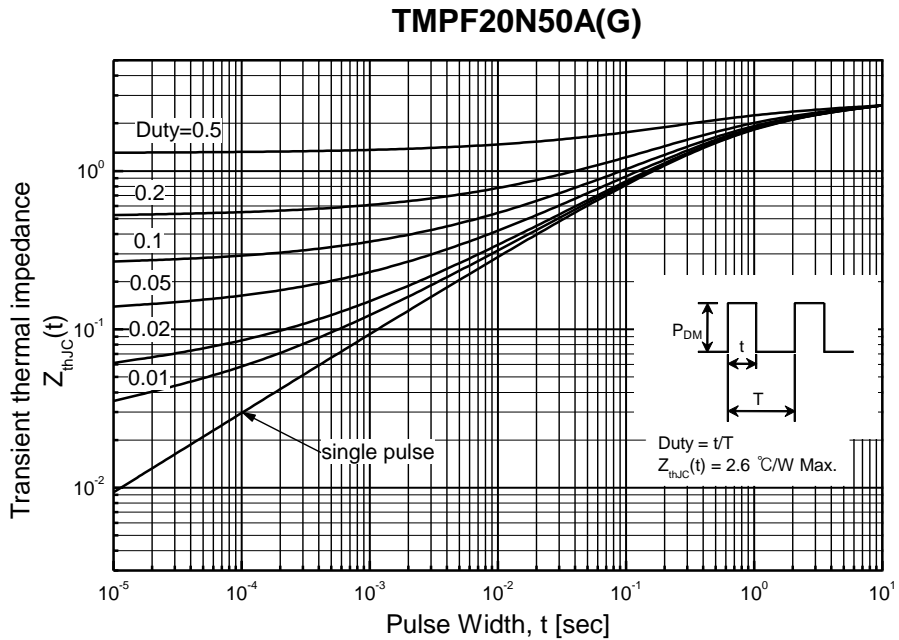
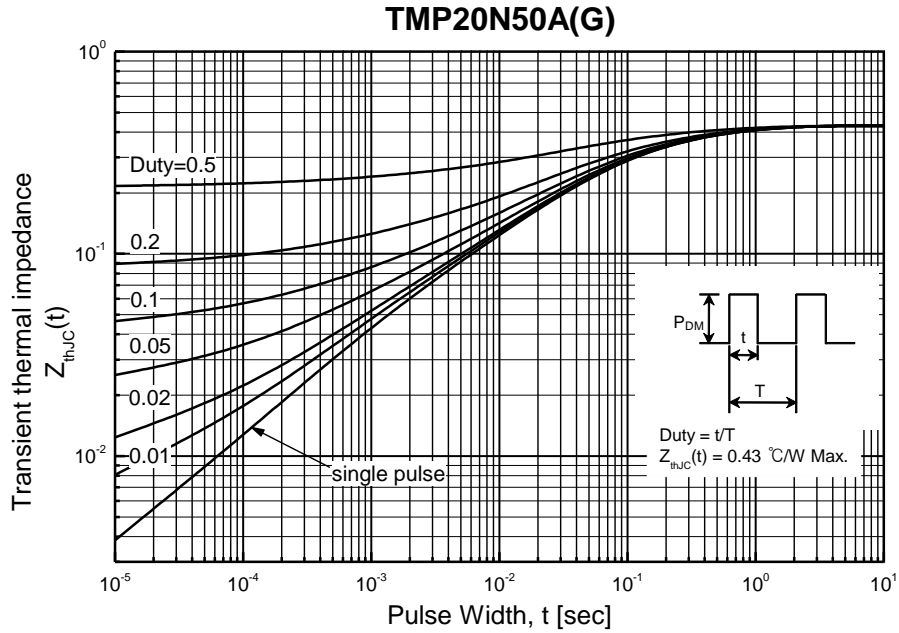


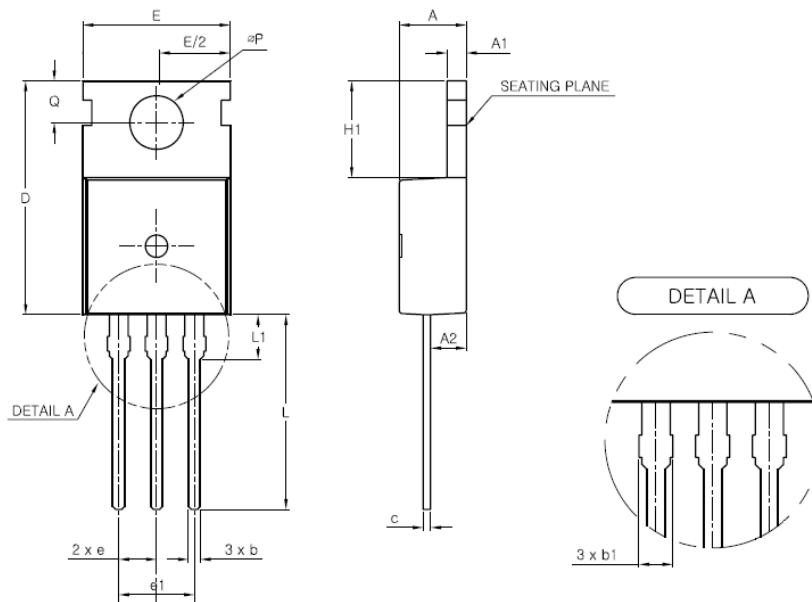
### TMP20N50A(G)



### TMPF20N50A(G)

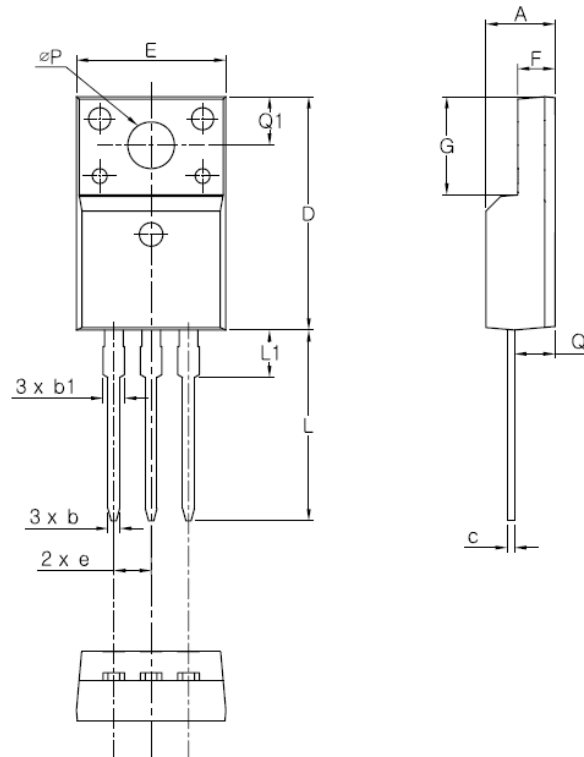




**TO-220AB-3L MECHANICAL DATA**


SYMBOL	MIN	MAX
A	4.30	4.70
A1	1.22	1.40
A2	2.20	2.79
b	0.70	0.91
b1	1.15	1.62
c	0.36	0.60
D	14.99	15.90
E	9.70	10.41
e	2.54 TYP	
e1	5.08 BSC	
H1	5.97	6.70
L	12.88	13.97
L1	3.31	3.81
$\varnothing P$	3.40	3.88
Q	2.60	2.90

## TO-220F-3L MECHANICAL DATA



SYMBOL	MIN	MAX
A	4.50	4.93
b	0.70	0.91
b1	1.15	1.47
c	0.36	0.60
D	15.67	16.07
E	6.96	10.36
e	2.54 BSC	
F	2.34	2.74
G	6.48	6.90
L	12.37	13.18
L1	2.23	3.43
Q	2.56	2.96
Q1	3.10	3.50
$\varnothing P$	2.98	3.38

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